

**IN THE ABSTRACT OF THE DISCLOSURE:**

Please amend the abstract of the disclosure as follows:

**Abstract of the Invention Disclosure**

~~The present invention relates to~~ In a method ~~for~~ of measuring a three dimensional shape of an arbitrary fine pattern on a semiconductor device. ~~An~~ an optical measurement system ~~measures~~ carries out a measurement to obtain cross-section information. ~~An~~ and an electron microscope obtains an electron beam image of the arbitrary fine pattern. Plane information and cross-section information obtained from the electron beam image of the arbitrary fine pattern are combined to measure the three dimensional shape of the arbitrary fine pattern.